

METHOD OF FABRICATING INVERTED PYRAMID ON CRYSTALLINE SILICON USING
LITHOGRAPHY FREE FABRICATION TECHNIQUE

Abstract:

The present invention proposes a method of lithography free inverted pyramid fabrication in silicon. The photolithography step required in conventional process for the fabrication of inverted pyramidal texturing in silicon has been eliminated. The entire lithography process is replaced by means of a thin film deposition process and an annealing step.

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